



IRLR2905PBF Information



For Reference Only

Part Number IRLR2905PBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single MOSFET N-CH 55V 42A DPAK

DescriptionMOSFET N-CH 55V 42A DPAK**Package**TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRLR2905PBF Specifications

Manufacturer Part Number IRLR2905PBF Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 42A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 48nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1700pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 110W (Tc) Rds On (Max) @ Id, Vgs 27 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Qate Charge (Qg) (Max) @ Vgs Hoput Capacitance (Ciss) (Max) @ Vds Vgs (Max) 1700pF @ 25V Vgs (Max) 110W (Tc) Rds On (Max) @ Id, Vgs Poerating Temperature -55°C ~ 175°C (TJ) Mounting Type Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer Part Number	IRLR2905PBF
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SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)55VCurrent - Continuous Drain (Id) @ 25°C42A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs48nC @ 5VInput Capacitance (Ciss) (Max) @ Vds1700pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs27 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) 55V Current - Continuous Drain (Id) @ 25°C 42A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Joperating Temperature Supplier Device Package Package / Case N-Channel MOSFET (Metal Oxide) MOSFET (Metal Oxide) 48NC @ 5V 42A (Tc) 48n (C e 5V 48n (C e	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 42A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case MOSFET (Metal Oxide) 55V MOUSFET (Metal Oxide) 55V 42A (Tc) 42	Series	HEXFET?
Drain to Source Voltage (Vdss)55VCurrent - Continuous Drain (Id) @ 25°C42A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs48nC @ 5VInput Capacitance (Ciss) (Max) @ Vds1700pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs27 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 42A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs 48nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1700pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 110W (Tc) Rds On (Max) @ Id, Vgs 27 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs48nC @ 5VInput Capacitance (Ciss) (Max) @ Vds1700pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs27 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	55V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1700pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 27 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Current - Continuous Drain (Id) @ 25°C	42A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1700pF @ 25V Vgs (Max) ±16V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 27 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	4V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±16V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 27 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max) $\pm 16V$ FET Feature-Power Dissipation (Max) $110W$ (Tc)Rds On (Max) @ Id, Vgs $27 \text{ mOhm } @ 25\text{A}, 10V$ Operating Temperature $-55^{\circ}\text{C} \sim 175^{\circ}\text{C}$ (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	48nC @ 5V
FET Feature - Power Dissipation (Max) 110W (Tc) Rds On (Max) @ Id, Vgs 27 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	1700pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 27 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±16V
Rds On (Max) @ Id, Vgs27 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	110W (Tc)
Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	27 mOhm @ 25A, 10V
Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	D-Pak
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

IRLR2905PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRLR2905PBF Payment Methods



















IRLR2905PBF Shipping Methods













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